

RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

FEATURES

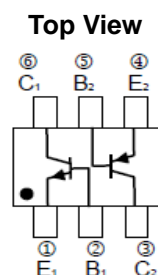
- Two transistors in one package
- Reduces number of components and board space
- No mutual interference between the transistors

MARKING :

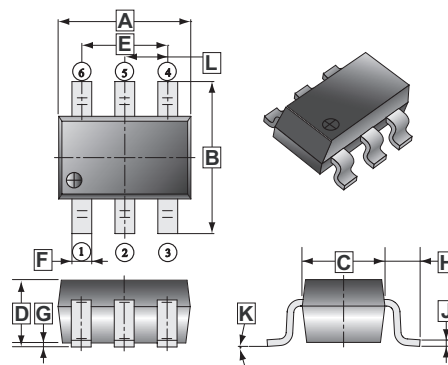
4Ft

PACKAGE INFORMATION

Package	MPQ	Leader Size
SOT-363	3K	7 inch



SOT-363



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.00	2.20	G	0.100 REF.	
B	2.15	2.45	H	0.525 REF.	
C	1.15	1.35	J	0.08	0.15
D	0.90	1.10	K	8°	
E	1.20	1.40	L	0.650 TYP.	
F	0.15	0.35			

ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{(BR)CBO}	80	V
Collector-Emitter Voltage	V _{(BR)CEO}	65	V
Emitter-Base Voltage	V _{(BR)EBO}	6	V
Collector Current	I _C	0.1	A
Collector Power Dissipation	P _C	200	mW
Junction & Storage Temperature	T _J , T _{STG}	150, -65~150	°C

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Collector-Base Breakdown Voltage	V _{(BR)CBO}	80	-	-	V	I _C =10μA, I _E =0
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	65	-	-		I _C =10mA, I _B =0
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	6	-	-		I _E =10μA, I _C =0
Collector Cut-Off Current	I _{CBO}	-	-	15	nA	V _{CB} =30V, I _E =0
Emitter Cut-Off Current	I _{EBO}	-	-	5	μA	V _{EB} =5V, I _C =0
DC Current Gain	h _{FE}	110	-	-		V _{CE} =5V, I _C =2mA
Collector-Emitter Saturation Voltage	V _{CE(sat)}	-	-	0.1	V	I _C =10mA, I _B =0.5mA
	V _{CE(sat)}	-	-	0.3	V	I _C =100mA, I _B =5mA
Base-Emitter Saturation Voltage	V _{BE(sat)}	-	0.77	-	V	I _C =10mA, I _B =0.5mA
Transition Frequency	f _T	100	-	-	MHz	V _{CB} =5V, I _E =10mA, f=100MHz
Collector Output Capacitance	C _{ob}	-	-	1.5	pF	V _{CB} =10V, I _E =0, f=1MHz